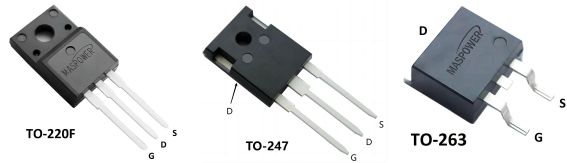


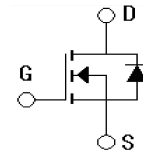
Features

- $V_{DS}=1000V, I_D=15A$
- Low C_{rss}
- Low gate charge
- Improved dv/dt capability



Applications

- High efficiency switch mode power supplies
- Electronic lamp ballasts based on half bridge
- UPS



Absolute Ratings ($T_C=25^\circ C$)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DSS}	1000	V
Transient Gate-Source Voltage	V_{GSM}	± 30	V
Continuous Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current-continuous	I_D	$T_C=25^\circ C$	A
		$T_C=100^\circ C$	
Drain Current-pulse ⁽¹⁾	I_{DM}	60*	A
Single Pulsed Avalanche Energy ⁽²⁾	E_{AS}	500	mJ
Maximum Power Dissipation (TO-220F)	P_D	70	W
		0.56	W/ $^\circ C$
Maximum Power Dissipation (TO-247, TO-263)	P_D	208	W
		1.67	W/ $^\circ C$
Operating and Storage Temperature Range	T_J, T_{STG}	-55~+150	$^\circ C$
Maximum Lead Temperature for Soldering Purposes	T_L	300	

*Pulse width Limited by safe operating area

Electrical Characteristics($T_{CASE}=25^\circ C$ unless otherwise specified)

Parameter	Symbol	Tests conditions	Min	Typ	Max	Units
Drain-Source Voltage	BV_{DSS}	$I_D=250\mu A, V_{GS}=0V$	1000	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=V_{DSS}, T_C=25^\circ C$	-	-	1	μA
		$V_{GS}=0V, T_C=125^\circ C$	-	-	100	μA
Gate-Body Leakage	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA

Current						
On-Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	3	4	5	V
Static Drain-Source On-Resistance ⁽³⁾	$R_{DS(on)}$	$V_{GS}=10V, I_D=5A$	-	0.52	0.65	Ω
Forward Transconductance ⁽³⁾	g_{fs}	$V_{DS}=40V, I_D=5A$	-	0.82	-	S
Dynamic Characteristics						
Input capacitance	C_{iss}	$V_{DS}=25V,$ $V_{GS}=0V,$ $f=1.0MHz^{(4)}$	-	1500	-	pF
Output capacitance	C_{oss}		-	110	-	pF
Reverse transfer capacitance	C_{rss}		-	10	-	pF

Electrical Characteristics($T_{CASE}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Tests conditions	Min	Typ	Max	Units
Switching-Characteristics						
Turn-On delay time	t _{d(on)}	V _{DS} =500V,I _D =15A, V _{GS} =10V,R _G =25Ω	-	30	-	ns
Turn-On rise time	t _r		-	26	-	ns
Turn-Off delay time	t _{d(Off)}		-	80	-	ns
Turn-Off rise time	t _f		-	22	-	ns
Total Gate Charge	Q _g	V _{DS} =500V,I _D =15A, V _{GS} =10V ⁽⁴⁾	-	26	-	nC
Gate-Source charge	Q _{gs}		-	5	-	nC
Gate-Drain charge	Q _{gd}		-	15	-	nC
Drain-Source Diode Characteristics and Maximum Ratings						
Maximum Continuous Drain-Source Diode Forward Current	V _{SD}	V _{GS} =0V,I _S =5A	-	0.82	1.2	V
Diode Forward Current	I _S		-	-	15	A
Reverse recovery time	T _{rr}	I _S =15A,di _F /dt=100A/μs VR=100V,V _{GS} =0V	-	350	-	ns
Reverse recovery charge	Q _{rr}		-	2634	-	nC
Reverse recovery current	I _{rr}		-	14	-	A

Thermal Characteristics

Parameter	Symbol	Value		Unit
		TO-220F	TO-247/ TO-263	
Thermal Resistance, junction to Case	$R_{th(j-C)}$	1.78	0.6	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, junction to Ambient	$R_{th(j-A)}$	62.5	50	$^{\circ}\text{C}/\text{W}$

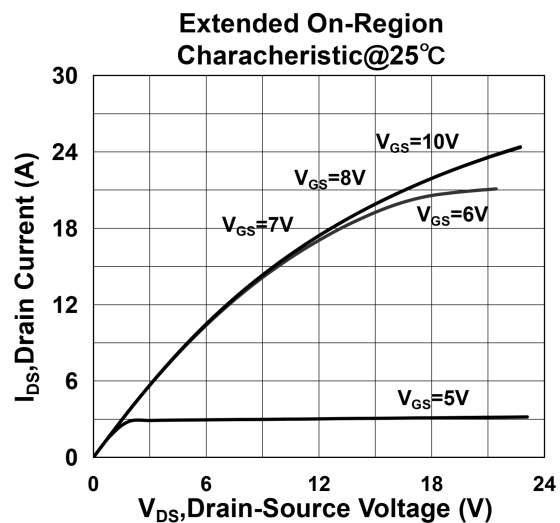
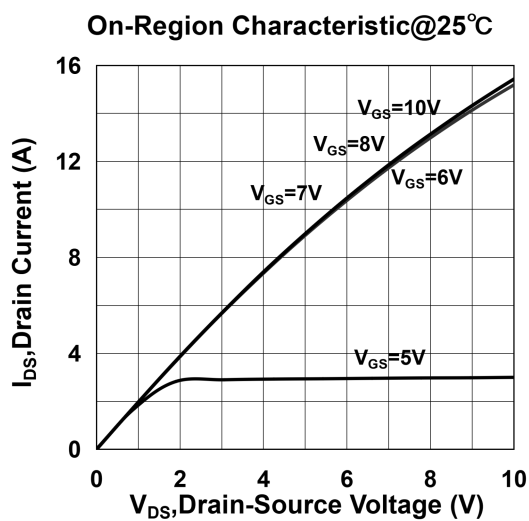
Order information

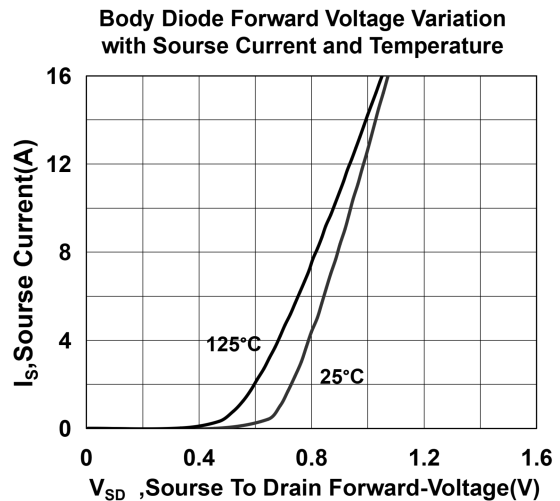
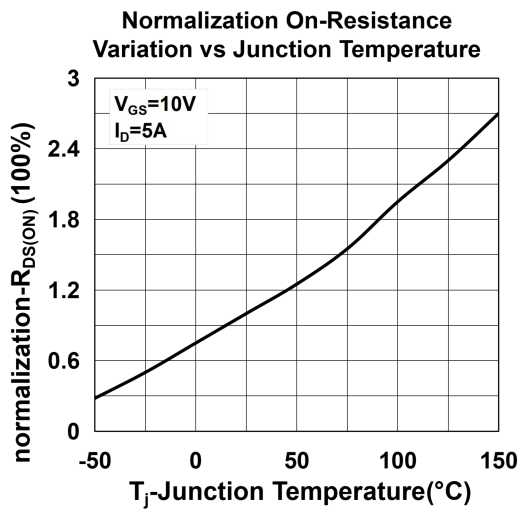
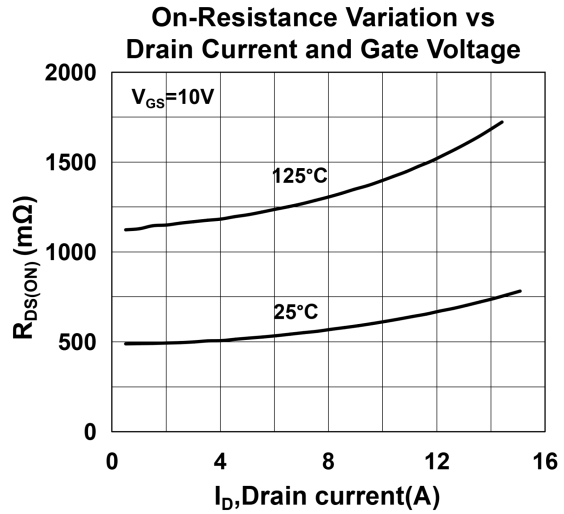
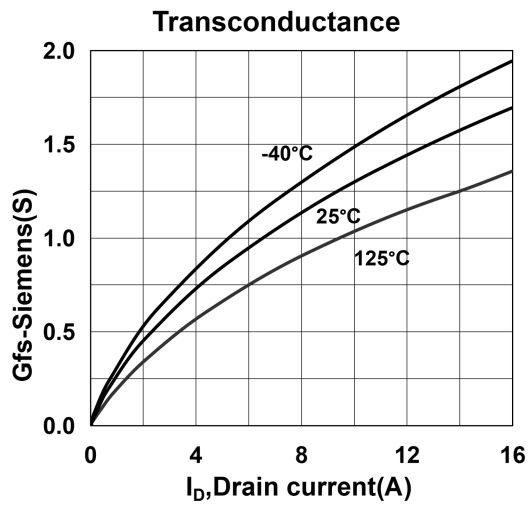
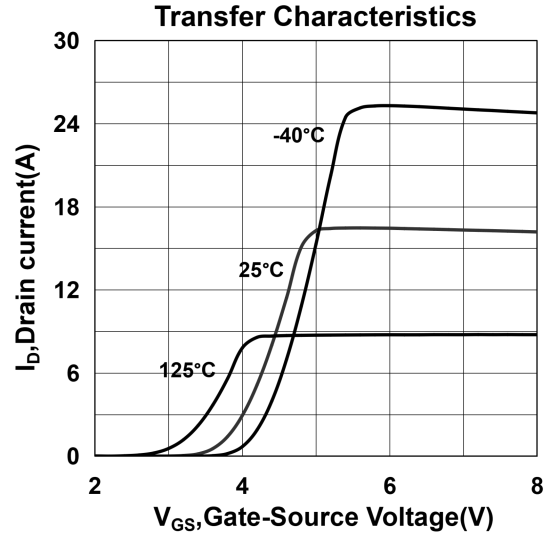
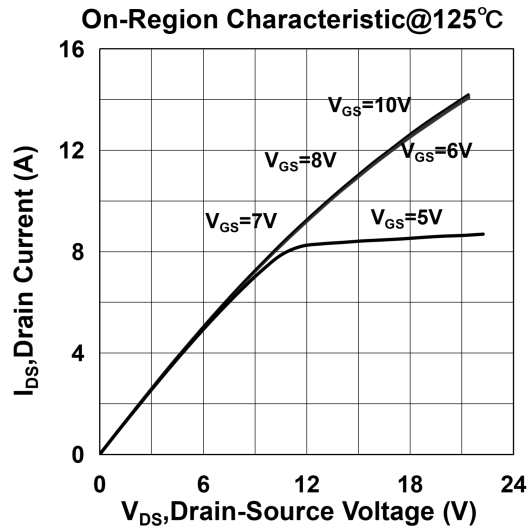
Order codes	Package	Packaging
MS15N100HCT1	TO-220F	Tube
MS15N100HCC0	TO-247	Tube
MS15N100HCE0	TO-263	

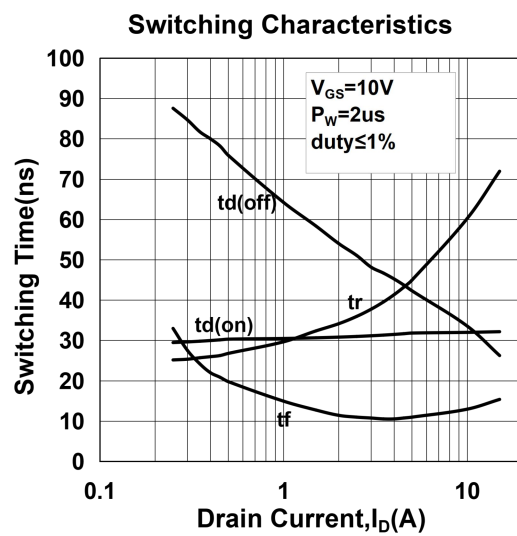
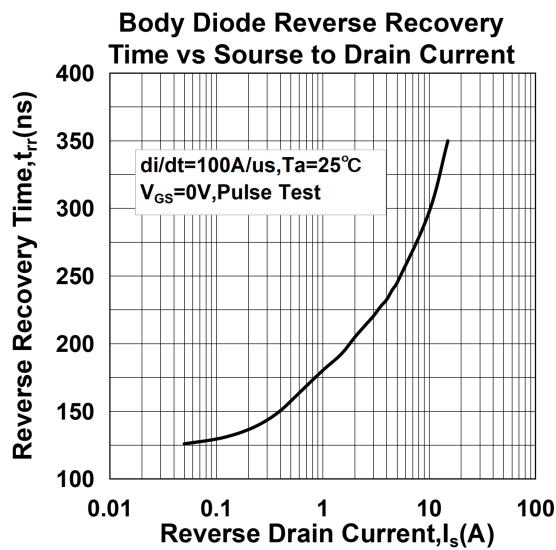
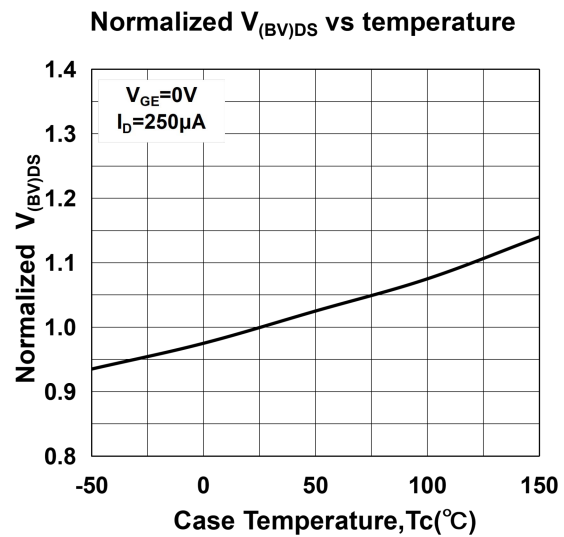
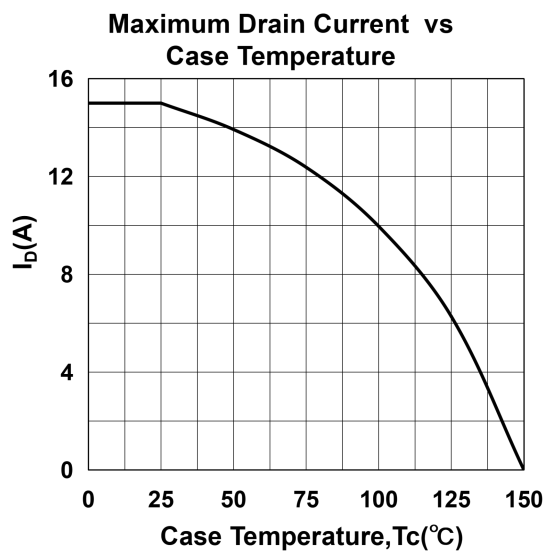
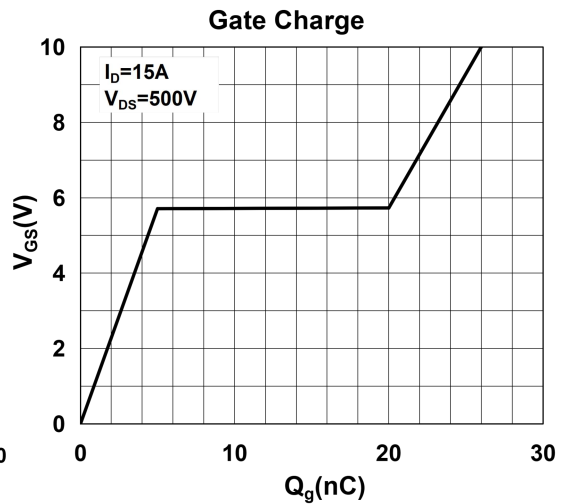
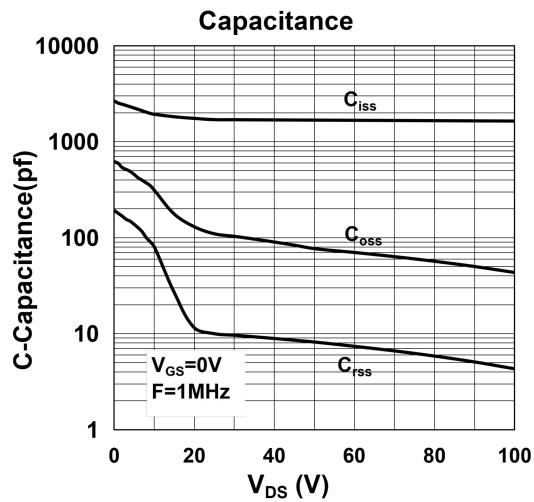
Notes:

- 1: Pulse width limited by maximum junction temperature
- 2: $L=10\text{mH}$, $I_{AS}=10\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\Omega$, Starting $T_J=25^{\circ}\text{C}$
- 3: Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$
- 4: Essentially independent of operating temperature

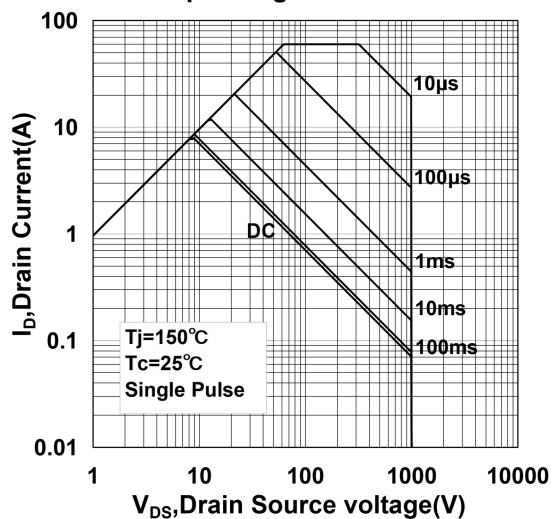
Electrical Characteristics



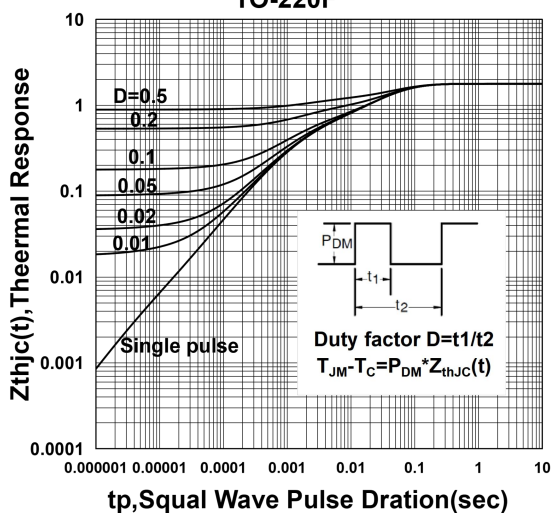




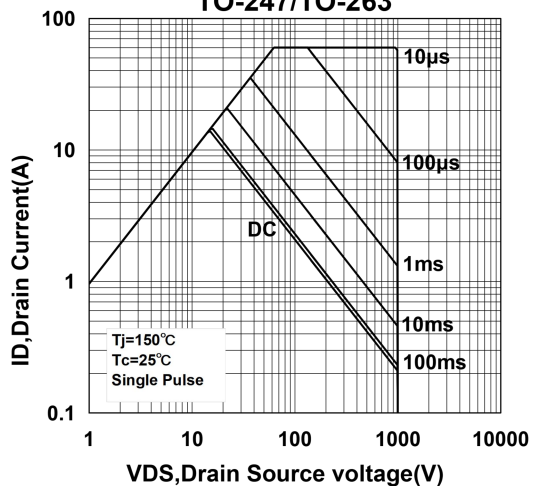
Safe Operating Area for TO-220F



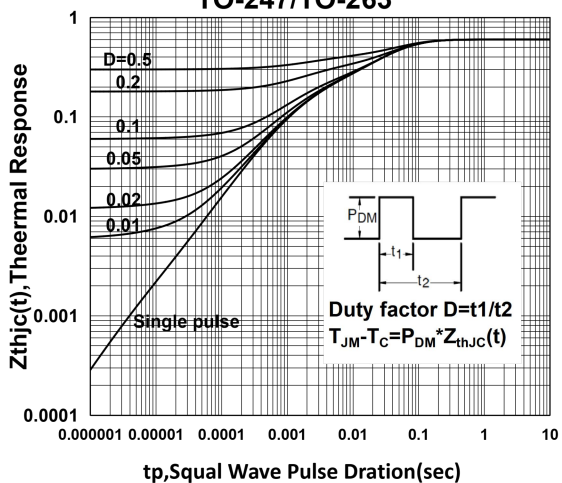
Transient response Curve for TO-220F



Safe Operating Area for TO-247/TO-263



Transient response Curve for TO-247/TO-263



Package Mechanical Data

